CMLM0705

MULTI DISCRETE MODULE™

SURFACE MOUNT
SILICON SWITCHING PNP TRANSISTOR
AND
LOW V_F SILICON SCHOTTKY DIODE

PICOmini™ MDM™ Multi Discrete Module



SOT-563 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLM0705 is a Multi Discrete Module™ consisting of a single PNP Transistor and a Schottky Diode packaged in a space saving PICOmini™ SOT-563 case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

- Combination: Small Signal Switching PNP Transistor and Low V_F Schottky Diode.
- Complementary Device: **CMLM2205**

MARKING CODE: C75

MAXIMUM RATINGS - CASE: (T_A=25°C)	**SYMBOL**		**UNITS**
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W
MAXIMUM RATINGS - Q1: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	90	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Continuous Collector Current	I_C	600	mA
MAXIMUM RATINGS - D1: (T_A=25°C)	**SYMBOL**		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	500	mA
Peak Repetitive Forward Current, tp≤1.0ms	I_{FRM}	3.5	A
Peak Forward Surge Current, tp=8.0ms	I_{FSM}	10	A

ELECTRICAL CHARACTERISTICS - Q1: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=50V			10	nA
I_{CBO}	V_{CB}=50V, T_A=125°C			10	µA
I_{CEV}	V_{CE}=30V, V_{BE}=0.5V			50	nA
BV_{CBO}	I_C=10µA	90	115		V
BV_{CEO}	I_C=10mA	60			V
BV_{EBO}	I_E=10µA	5.0			V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA		0.113	0.2	V
$V_{CE(SAT)}$	I_C=500mA, I_B=50mA		0.280	0.7	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA			1.3	V
$V_{BE(SAT)}$	I_C=500mA, I_B=50mA			2.6	V
h_{FE}	V_{CE}=10V, I_C=0.1mA	100	205		
h_{FE}	V_{CE}=10V, I_C=1.0mA	100			
h_{FE}	V_{CE}=10V, I_C=10mA	100			
h_{FE}	V_{CE}=10V, I_C=150mA	100		300	
h_{FE}	V_{CE}=10V, I_C=500mA	75	110		

CMLM0705

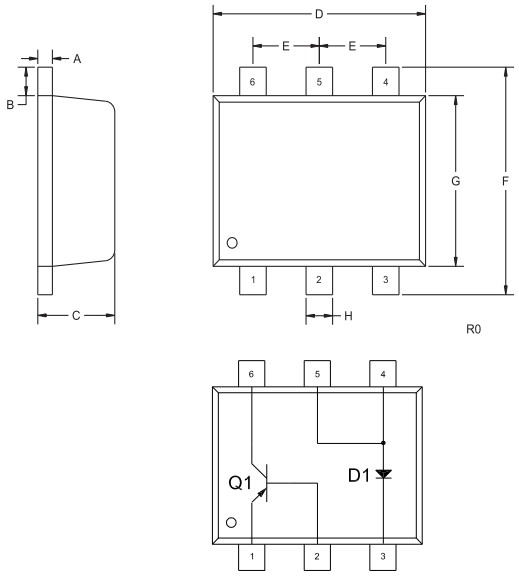
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ELECTRICAL CHARACTERISTICS - Q1 - Continued:

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	V_{CE}=20V, I_C=50mA, f=100MHz	200		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		8.0	pF
C_{ib}	V_{BE}=2.0V, I_C=0, f=1.0MHz		30	pF
t_{on}	V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA		45	ns
t_d	V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA		10	ns
t_r	V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA		40	ns
t_{off}	V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA		100	ns
t_s	V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA		80	ns
t_f	V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA		30	ns
ELECTRICAL CHARACTERISTICS - D1: (T_A=25°C)				
I_R	V_R=10V		20	μA
I_R	V_R=30V		100	μA
BV_R	I_R=500μA	40		V
V_F	I_F=100μA		0.13	V
V_F	I_F=1.0mA		0.21	V
V_F	I_F=10mA		0.27	V
V_F	I_F=100mA		0.35	V
V_F	I_F=500mA		0.47	V
C_T	V_R=1.0V, f=1.0MHz		50	pF

SOT-563 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:
1) Emitter Q1
2) Base Q1
3) Cathode D1
4) Anode D1
5) Anode D1
6) Collector Q1

MARKING CODE: C75

R1 (18-January 2010)